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Sheet 1 of 1

FORM PTO-1449 (SUBSTITUTE)  U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))	Attorney Docket No.: GR 98 P 5874 P	Applic. No. 09/873,227
	Applicant Daniel Reznik	
	Filing Date June 4, 2001	Group Art Unit 2822

U.S. PATENT DOCUMENTS

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	A	5,608,237	03/04/97	Aizawa et al			
	B	5,766,966	06/16/98	Ng			
	C						
	D						
	E						
	F						
	G						
	H						
	I						

FOREIGN PATENT DOCUMENT

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES   NO
	J	0 837 508 A2	04/22/98	Europe			X
	K	WO 98/38681	09/03/98	WIPO			X
	L						
	M						
	N						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

	O	M. Mori et al.: "A Novel High-Conductivity IGBT (HiGT) with a Short Circuit Capability", <i>Proceedings of 1998 International Symposium on Power Semiconductor Devices &amp; ICs, Kyoto, Japan, pp. 429-432, XP-000801108</i>
	P	
EXAMINER		
DATE CONSIDERED		2/4/03

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.